

#### LOW VCE(SAT) NPN SURFACE MOUNT TRANSISTOR

#### **Features**

- BV<sub>CEO</sub> > 50V
- I<sub>C</sub> = 3.0A Continuous Current
- Complementary PNP Type Available (DPLS350Y)
- Ideally Suited for Automated Assembly Processes
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

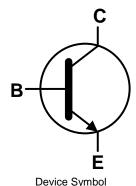
#### **Mechanical Data**

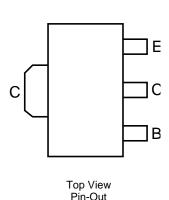
- Case: SOT89
- Case Material: Molded Plastic, "Green" Molding Compound UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (23)
- Weight: 0.052 grams (Approximate)

### **Applications**

Ideal for Medium Power Switching or Amplification Applications







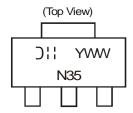
### Ordering Information (Note 4)

Device	Package	Shipping
DNLS350Y-13	SOT89	2500/Tape & Reel

Notes::

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



D | |= Manufacturer's Marking N35 = Product Type Marking Code YWW = Date Code Marking Y = Last Digit of Year (ex: 7 = 2017) WW = Week Code (01 to 52)



## Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	50	V
Collector-Emitter Voltage	V <sub>CEO</sub>	50	V
Emitter-Base Voltage	V <sub>EBO</sub>	5	V
Peak Pulse Collector Current	I <sub>CM</sub>	5	А
Continuous Collector Current	I <sub>C</sub>	3	Α
Base Current	I <sub>B</sub>	0.5	Α

### Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5) @ T <sub>A</sub> = 25°C	P <sub>D</sub>	1	W
Thermal Resistance, Junction to Ambient Air (Note 5) @ T <sub>A</sub> = +25°C	$R_{ heta JA}$	125	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

#### ESD Ratings (Note 6)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	٧	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

# **Thermal Characteristics and Derating Information**

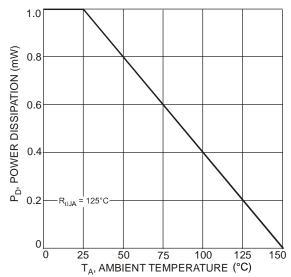


Fig. 1 Max Power Dissipation vs. Ambient Temperature

<sup>5.</sup> For a device mounted with the collector lead on 15mm x 15mm 1oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.

<sup>6.</sup> Refer to JEDEC specification JESD22-A114 and JESD22-A115.



## **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Collector-Base Cutoff Current	lana	_	_	100	nA	$V_{CB} = 50V, I_{E} = 0$
Collector-base Cutoff Current	I <sub>CBO</sub>	_	_	50	μΑ	$V_{CB} = 50V, I_E = 0, T_A = +150$ °C
Emitter-Base Cutoff Current	I <sub>EBO</sub>	_	_	100	nA	$V_{EB} = 5V, I_{C} = 0$
Collector-Emitter Cutoff Current	I <sub>CES</sub>	_	_	100	nA	$V_{CE} = 50V, V_{BE} = 0$
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	50	_		V	$I_C = 100 \mu A$
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	50		_	V	$I_C = 10mA$
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	5	_	_	V	$I_E = 100 \mu A$
ON CHARACTERISTICS (Note 7)						
		300	_			$V_{CE} = 2V, I_{C} = 0.1A$
		300	_	_		$V_{CE} = 2V, I_{C} = 0.5A$
DC Current Gain	h <sub>FE</sub>	300		700		$V_{CE} = 2V$ , $I_C = 1A$
		200	_	_		$V_{CE} = 2V$ , $I_C = 2A$
		100	_	_		$V_{CE} = 2V$ , $I_C = 3A$
		_	38	80		$I_C = 0.5A, I_B = 50mA$
		_	70	160		$I_C = 1A$ , $I_B = 50mA$
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	_	130	280	mV	$I_C = 2A$ , $I_B = 100mA$
		_	124	260		$I_C = 2A$ , $I_B = 200mA$
		_	180	370		$I_C = 3A$ , $I_B = 300mA$
Equivalent On-Resistance	R <sub>CE</sub> (SAT)	_	62	130	mΩ	$I_E = 2A$ , $I_B = 200mA$
Base Emitter Seturation Voltage		_	_	1.1	V	$I_C = 2A$ , $I_B = 100mA$
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	_	_	1.2	V	$I_C = 3A$ , $I_B = 300mA$
Base-Emitter Turn-on Voltage	V <sub>BE(ON)</sub>	_	_	1.1	V	V <sub>CE</sub> = 2V, I <sub>C</sub> = 1A
SMALL SIGNAL CHARACTERISTICS						
Transition Frequency	f <sub>T</sub>	100	_	_	MHz	V <sub>CE</sub> = 5V, I <sub>C</sub> = 100mA, f = 100MHz
Output Capacitance	C <sub>obo</sub>	_	_	25	pF	V <sub>CB</sub> = 10V, f = 1MHz

Notes: 7. Measured under pulsed conditions. Pulse width =  $300\mu s$ . Duty cycle  $\leq 2\%$ .



## Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

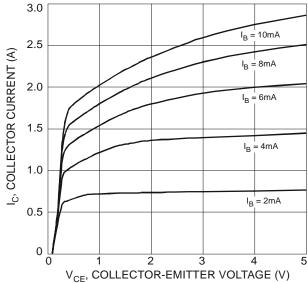


Fig. 2 Typical Collector Current vs. Collector-Emitter Voltage

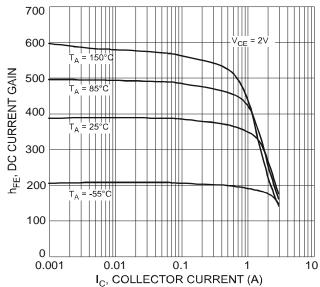
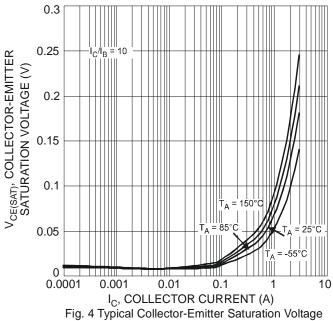


Fig. 3 Typical DC Current Gain vs. Collector Current



vs. Collector Current

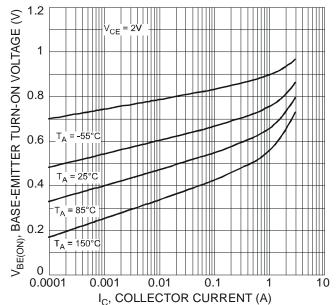
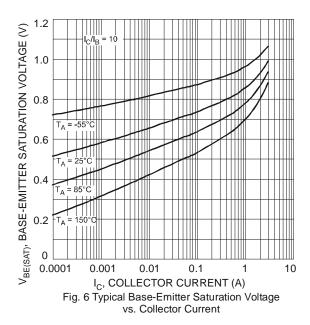


Fig. 5 Typical Base-Emitter Turn-On Voltage vs. Collector Current



# Typical Electrical Characteristics ( $@T_A = +25^{\circ}C$ , unless otherwise specified.) (Cont.)



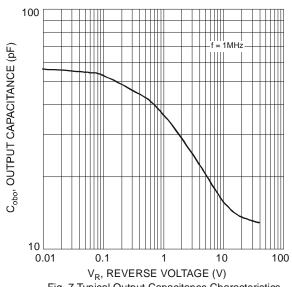
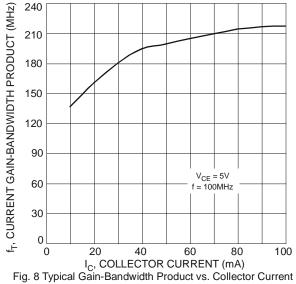


Fig. 7 Typical Output Capacitance Characteristics

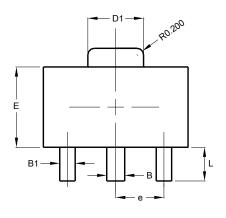


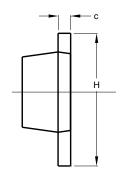


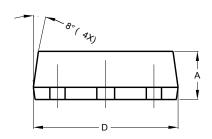
## **Package Outline Dimensions**

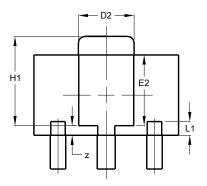
Please see http://www.diodes.com/package-outlines.html for the latest version.

#### **SOT89**







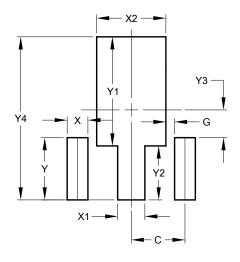


SOT89						
Dim	Min	Max	Тур			
Α	1.40	1.60	1.50			
В	0.50	0.62	0.56			
B1	0.42	0.54	0.48			
С	0.35	0.43	0.38			
D	4.40	4.60	4.50			
D1	1.62	1.83	1.733			
D2	1.61	1.81	1.71			
Е	2.40	2.60	2.50			
E2	2.05	2.35	2.20			
е	-	-	1.50			
Н	3.95	4.25	4.10			
H1	<b>H1</b> 2.63		2.78			
L	0.90	1.20	1.05			
L1	0.327	0.527	0.427			
Z	0.20	0.40	0.30			
All Dimensions in mm						

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT89



Dimensions	Value (in mm)
С	1.500
G	0.244
Χ	0.580
X1	0.760
X2	1.933
Υ	1.730
Y1	3.030
Y2	1.500
Y3	0.770
Y4	4.530

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